

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In Re PATENT APPLICATION OF:

Tien-Jen Cheng et al.

Appln. No.: 10/707,892

Art Unit: 2815

Filed: January 21, 2004

Examiner: M. C. Landau

For: DEVICE WITH PROBABLE AREA  
ARRAY PADS

**DECLARATION UNDER 37 C.F.R. §1.131**

Mail Stop **AMENDMENT**  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

We, Tien-Jen Cheng, David E. Eichstadt, Jonathan H. Griffith, Sarah H. Knickerbocker, Samuel R. McKnight, Kamallesh K. Srivastava, Kevin S. Petrarca, and Roger A. Quon, inventors for the invention claimed in the above referenced patent application, declare as follows:

Sometime prior to September 18, 2003, we conceived area array pads (hereinafter "Pads") that, when included on a device, such as a semiconductor device and/or structure, may be used for test probing the device;

Attached hereto and marked Exhibit A, is a copy of a presentation explaining our Pads, formation of the Pads, and test results of the Pads, all dates having been redacted therefrom, providing evidence of conception and reduction to practice;

As evidenced in pages 3 and 4 – 6 of Exhibit A, our Pads included:

- a terminal metal layer disposed on a passivating layer;
- a diffusion barrier layer on said terminal metal layer;
- a conducting layer pad on said diffusion barrier;
- a hard test barrier layer on, and enclosing (see page 6 of Exhibit A), said conducting layer pad, wherein said hard test barrier layer extends along the sides of said conducting layer pad and said conducting layer pad is completely enclosed by said diffusion barrier layer and said hard test barrier layer; and
- a plate passivating layer on said hard test barrier layer;

Sometime prior to September 18, 2003, we reduced our invention to practice as evidenced in pages 8 – 10 of Exhibit A;

All acts, including conception and reduction to practice, occurred in the United States;

We further declare that all statements made herein of our own knowledge are true and that all statements made on information and belief are believed to be true; and

We further declare that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Declaration Under 37 C.F.R. §1.131

FIS920030352US1  
Serial No. 10/707,892

Inventor: Tien-Jen Cheng

Signature: Tien-Jen Cheng Date: 10/26/2007  
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Signature: \_\_\_\_\_ Date: \_\_\_\_\_  
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Inventor: Jonathan H. Griffith

Signature: Jonathan H. Griffith Date: 10/29/2007  
Residence: 8 Budd Lane, Lagrangeville, New York 12540  
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Inventor: Sarah H. Knickerbocker

Signature: Sarah H. Knickerbocker Date: 10/26/07  
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Inventor: Samuel R. McKnight

Signature: \_\_\_\_\_ Date: \_\_\_\_\_

Residence: 112 Bruynswick Rd., New Paltz, New York, 12561  
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Inventor: Kevin S. Petrarca

Signature: \_\_\_\_\_ Date: \_\_\_\_\_

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Inventor: Kamalesh K Srivastava

Signature: Kamalesh K Srivastava Date: 10.26.07

Residence: 319 Sheafe Rd., Wappingers Falls, New York 12590  
Citizenship: USA

Post Office Address: Same as residence

Inventor: Roger A. Quon

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Residence: 15 Rockefeller Lane, Rhinebeck, New York 12572  
Citizenship: US

Post Office Address: Same as Residence



*Detailed Embodiment*

Disclosure F [REDACTED] 067

EXHIBIT A

FIS920030352US1  
Serial No. 10/707,892

## Problem Statement:

No Technology or Method exists for testing device performance on area-array, non-compliant metallurgies.

- Testing device performance directly on C4s is common practice, but is destructive
- Testing device performance on FBEOI via metallurgies is possible, but is also disruptive to bumping processes

## Proposal

A Means and Method for testing device performance on non-compliant metallurgies which also serve as a C4 ball-limiting metallurgy for bumping after test.

Silicon Interconnect Advanced Process Technology

R. Quon, S. McKnight, T. Cheng, D. Eichstadt, S. Knickerbocker, K. Srivastava, K. Petrarca, J. Griffith



technology

Microelectronics Division

Disclosure F [REDACTED] 067

EXHIBIT A

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Serial No. 10/707,892

Deform C4s

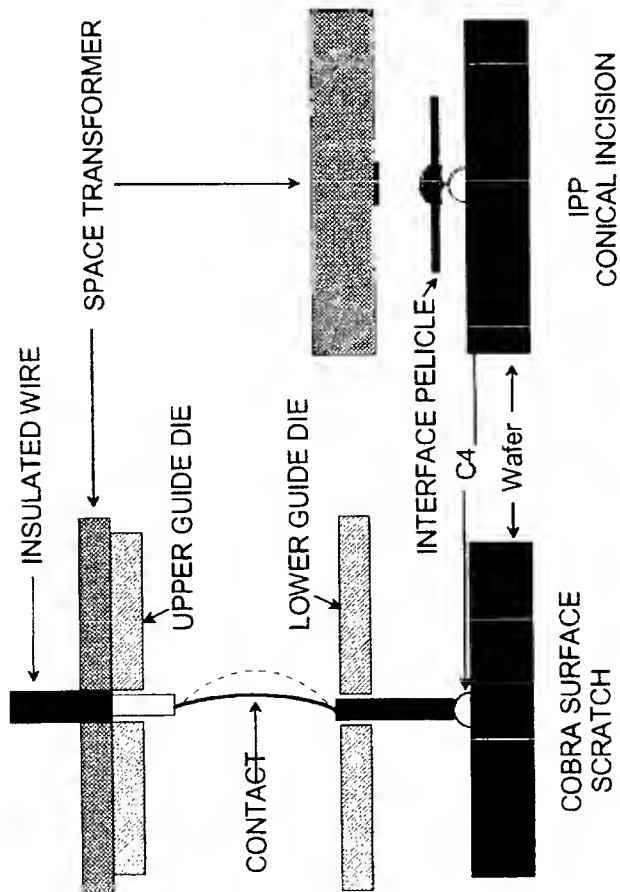


Standard Test Methods

Cobra probe mark on PB  
free C4



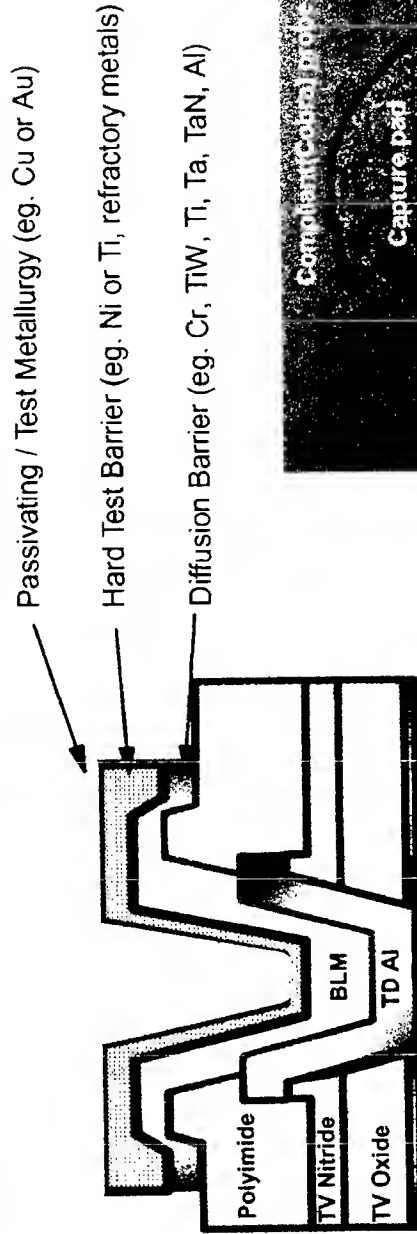
TFI probe mark on PbSn  
C4





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# essential elements of a bump metallurgy for test



bump metallurgy tested!

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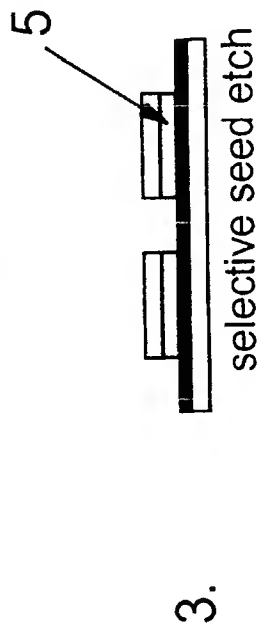
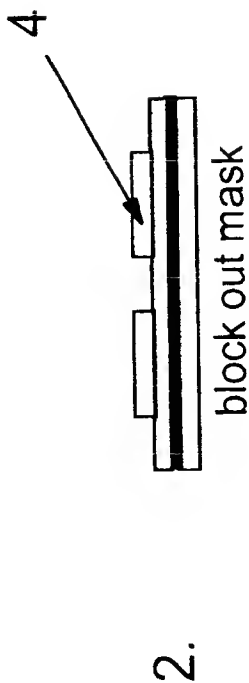
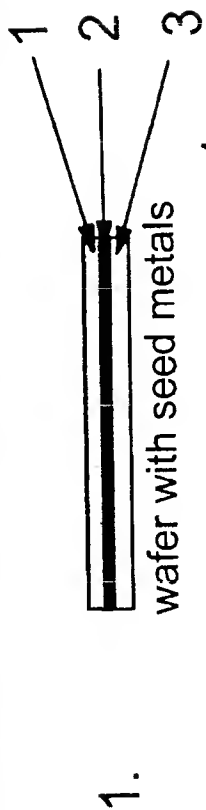
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Microelectronics Division

Disclosure File # [REDACTED] 067

EXHIBIT A

## Process Flow: Preferred Embodiment



### structures

1. seed metals commonly terminating in copper
2. barrier and/or adhesion metallurgy  
e.g. TiW, Ti, Ta, TaN, and so on.
3. substrate
4. patterned resist selectively blocking seed metal
5. copper pad

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EXHIBIT A

### Process Flow:

4.



5.



6.



structures

2. adhesion/barrier metallurgy serves as plating conducting layer
6. Plate hard test barrier metallurgy (eg. Ni) or exposed copper seed.
7. application of nickel barrier metallurgy, or other similar metal on which solder can be plated

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Process Flow:

8

7.



Sub-etch diffusion barrier

structures

8. Sub-etch the diffusion barrier to form the final test metallurgy.

While this method of constructing the test metallurgy is preferred, those skilled in the art could clearly construct the test structure by other means, including, but not limited to thru-hole plating and metal evaporation. These techniques are also encompassed in the spirit of this embodiment.

Silicon Interconnect Advanced Process Technology

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**technology**

Microelectronics Division

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EXHIBIT A

FIS920030352US1  
Serial No. 10/707,892

## Invention and Advantages:

### Enables MD Foundry

- Capability for wafer-level test prior to bumping offers customers more options for bumping and assembly
- Area-Array Testing on C4 UBM allow MD to track and optimize yields for Foundry Customers

### Enhances Test Capability

- Improved signals for measurements as contact resistance between probe and non-compliant metallurgy is LOWER than typical.
- Less force required to make good electrical contact **ENABLES** Multi-Die Testing from a force perspective
- Less clean and prep work required **REDUCES** test cycles.

### Enable Test Ability for Fine Pitch Designs

- Testing on Pads precludes Deformation and Bulging of solder

Silicon Interconnect Advanced Process Technology

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ASG

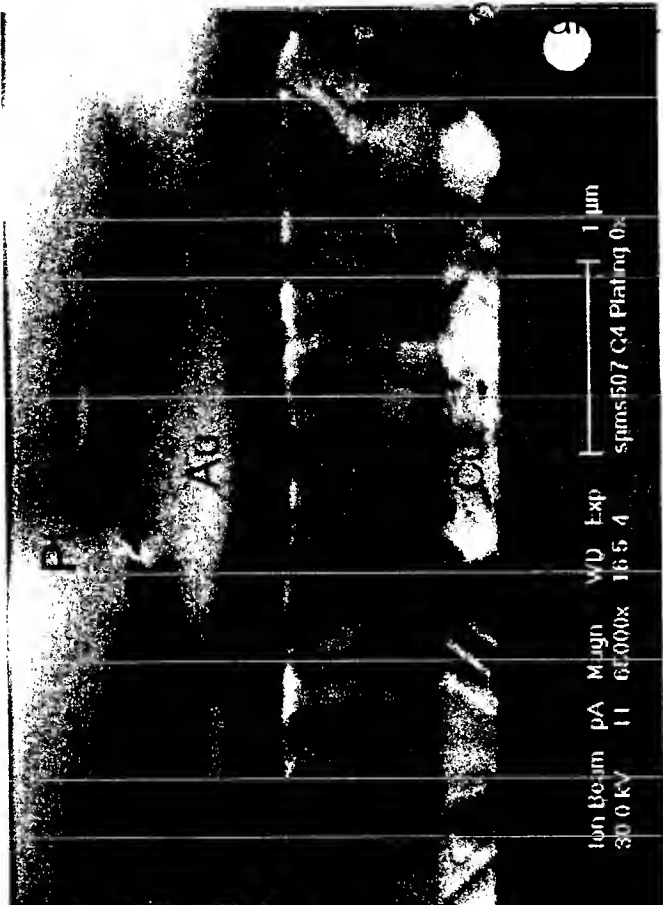
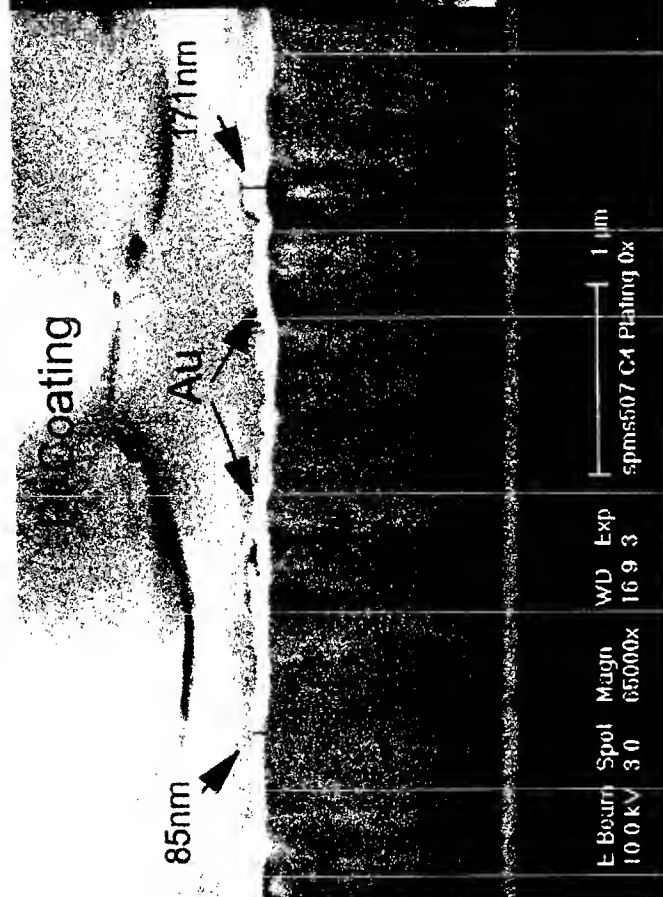
# C4 Plating BLM Layer Measurements

FIB Analysis

EXHIBIT A

Electron Image

Ion Image



0x REFLOWS

ASG

# C4 Plating BLM Layer Measurements

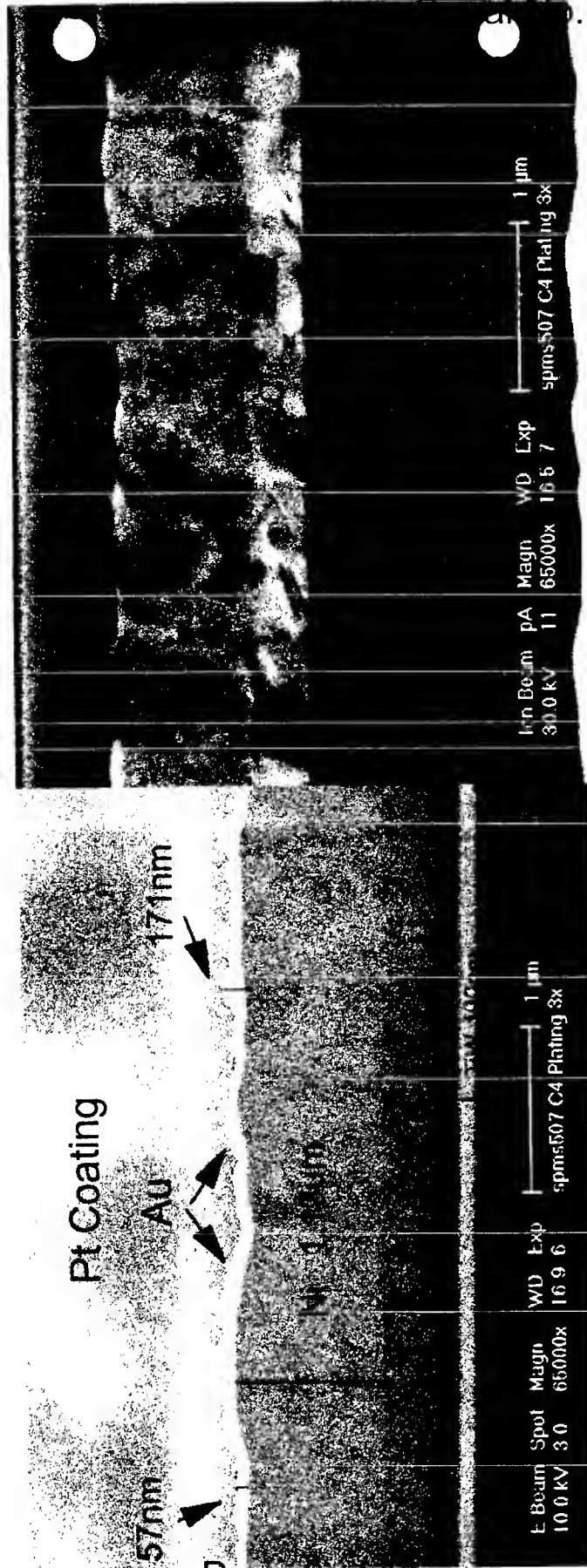
FIB Analysis

EXHIBIT A

FIS920030352US1  
10/707,892

Electron Image

Ion Image



3X REFLOWS

ASG

# C4 Plating BLM Layer Measurements

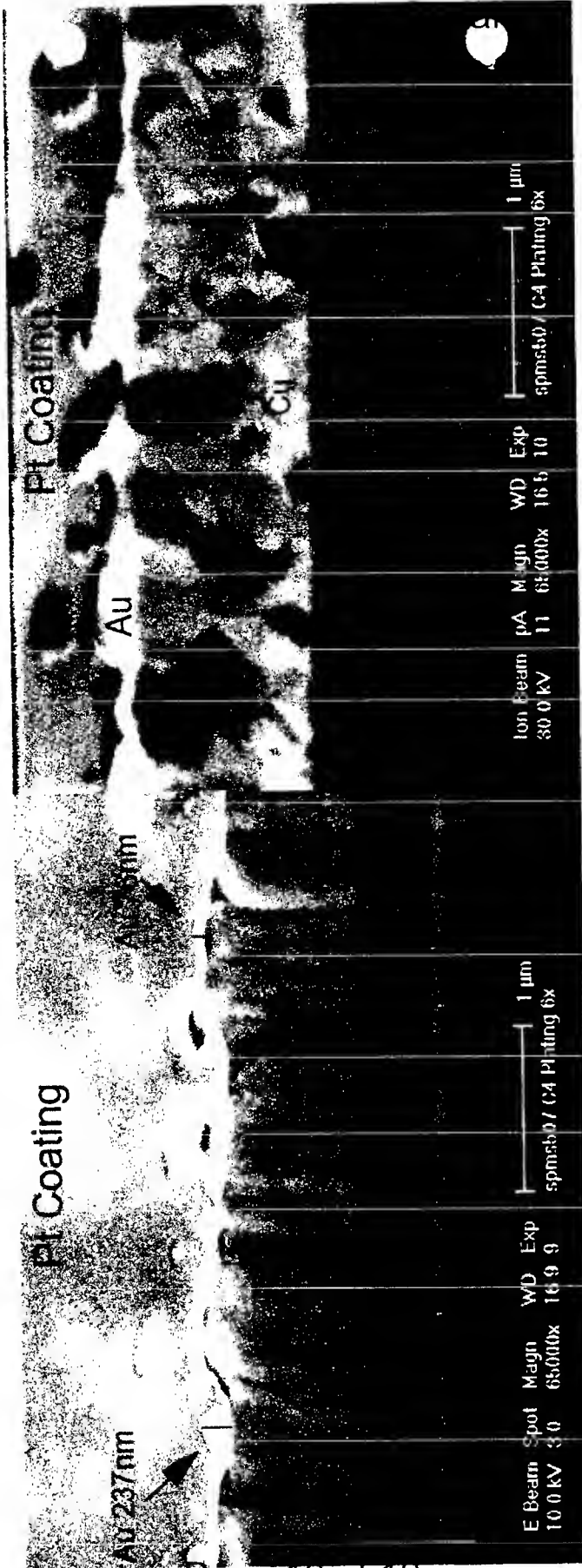
FIB Analysis

EXHIBIT A

FIS920030352US1  
10/707,892

Electron Image

Ion Image



6X REFLOWS

Declaration Under 37 C.F.R. §1.131

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Serial No. 10/707,892

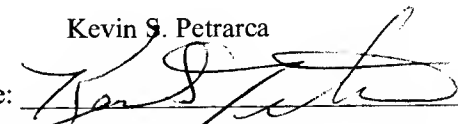
Inventor: Samuel R. McKnight

Signature: \_\_\_\_\_ Date: \_\_\_\_\_

Residence: 112 Bruynswick Rd., New Paltz, New York, 12561  
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Inventor: Kevin S. Petrarca

Signature:  \_\_\_\_\_ Date: 10/24/07

Residence: 28 Laurie Lane, Newburgh, New York, 12550  
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Inventor: Kamalesh K Srivastava

Signature: \_\_\_\_\_ Date: \_\_\_\_\_

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Citizenship: USA

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Signature: Samuel R. McKnight Date: 11/6/07Residence: 112 Bruynswick Rd., New Paltz, New York, 12561  
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Inventor: Jonathan H. Griffith

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